Surface modification of Fe\textsubscript{5}C\textsubscript{2} by binding silica-based ligand: A theoretical explanation of enhanced C\textsubscript{2} oxygenate selectivity

Junqing Yin\textsuperscript{a,c,*}, Shuyuan Wang\textsuperscript{b}, Dan Xu\textsuperscript{b}, Yong You\textsuperscript{a}, Xingchen Liu\textsuperscript{d}, Qing Peng\textsuperscript{e}

\textsuperscript{a} Institute of Advanced Study, Chengdu University, Chengdu 610106, China
\textsuperscript{b} Energy Research Institute, School of Energy and Power Engineering, Qilu University of Technology, Jinan 250014, China
\textsuperscript{c} National Energy Center for Coal to Liquids, Synfuels China Co., Ltd., Huairou District, Beijing 101400, China
\textsuperscript{d} State Key Laboratory of Coal Conversion, Institute of Coal Chemistry, Chinese Academy of Sciences, Taiyuan 030001, China
\textsuperscript{e} State Key Laboratory of Nonlinear Mechanics, Institute of Mechanics, Chinese Academy of Sciences, Beijing 100190, China

ABSTRACT

Elucidating the role(s) of support-like ligands remains a challenge in catalytic reaction like the Fischer-Tropsch Synthesis (FTS) catalyzed by the iron catalyst supported on silica. We herein theoretically investigated surface modification of Fe\textsubscript{5}C\textsubscript{2} by silica-based ligand and its influence on C\textsubscript{2} oxygenate selectivity in FTS, by carrying out DFT calculations on dissociation of CO and formations of CH\textsubscript{4} and C\textsubscript{2} on ha-SiO\textsubscript{2}/Fe\textsubscript{5}C\textsubscript{2}(510). To mimic the structure of surface modification, the ha-SiO\textsubscript{2}/Fe\textsubscript{5}C\textsubscript{2}(510) model was built up by binding the silica cluster (the ha-SiO\textsubscript{2} ligand) to Fe\textsubscript{5}C\textsubscript{2}(510). DFT calculations elucidated that the C + CH coupling with the lowest activation barrier among all the possible routes of C\textsubscript{2} formation on Fe\textsubscript{5}C\textsubscript{2}(510) is suppressed after modification with the ha-SiO\textsubscript{2} ligand because the binding ha-SiO\textsubscript{2} ligand limits the geometry relaxation caused by the C-CH coupling. However, CO molecule is anchored by the ha-SiO\textsubscript{2} ligand via hydrogen bond, suppressing the C-O cleavage because the d-valence band center of Fe\textsubscript{5}C\textsubscript{2}(510) lowers in energy by surface modification with the ha-SiO\textsubscript{2} ligand, but facilitating the C + CO coupling with the lowest activation barrier among all the possible routes of C\textsubscript{2} formation. Also, CH\textsubscript{4} formation in the ha-SiO\textsubscript{2}/Fe\textsubscript{5}C\textsubscript{2}(510) case is not so easy as that on Fe\textsubscript{5}C\textsubscript{2}(510). Therefore, C\textsubscript{2} oxygenate is formed more easily in the ha-SiO\textsubscript{2}/Fe\textsubscript{5}C\textsubscript{2}(510) case than in the Fe\textsubscript{5}C\textsubscript{2}(510) case. The result agrees with the experimental observation that C\textsubscript{2} oxygenate selectivity became high for iron-based FTS catalyst after surface modification of by silica-based ligand.

1. Introduction

Interface metal-support interaction (IMSI) is developed as a collective term describing effects introduced by the intimate contact between the metal and support, claimed from both the reducible and non-reducible supports [1–3]. The reducible supports often cause drastic changes in the shape and electronic properties, chemisorption properties, and catalytic performance of metal nanoparticles [4–6] while the influence of non-reducible supports on the catalytic performance is usually regarded to be not so obvious as that of reducible supports. However, silica, as a typical non-reducible support, plays an important role in improving resistance against sintering of iron-based catalysts in the industry of iron-based Fischer-Tropsch Synthesis (FTS) [7,8]. To improve the performance of traditional iron/silica catalyst, investigations have been made on the usage ratio of syngas [9], the activation conditions [10,11], the shape and size of particles [12,13], the composition of iron phases [14–16], and the promoter [17,18] and support effects [19,20] of catalyst itself. In these researches, it was found that silica influences the catalytic activity and catalytic selectivity in the FTS process [21–23]. For instance, CH\textsubscript{4} selectivity was improved when the Fe-based FTS catalyst incorporates with silica [24,25], whereas CH\textsubscript{4} selectivity decreases with a proper amount of silica in co-precipitated iron/silica catalysts [26]. The existed controversies are related to the variation of the iron-silica interface structure and other factors such as the changes in the size, morphology, and phase of iron species but it is hard to obtain the clear structure and evaluate the exact activity of iron-silica interface in practice [27–29]. It is indispensable to understand the electronic structure and catalytic activity of the iron-silica interface for tuning the performance of silica-supported iron-based (named iron/silica) FTS catalysts, but the knowledge is insufficient.

* Corresponding author at: Institute of Advanced Study, Chengdu University, Chengdu 610106, China.
E-mail address: yinjunqing@cdu.edu.cn (J. Yin).

https://doi.org/10.1016/j.mcat.2023.113333
Received 15 March 2023; Received in revised form 5 June 2023; Accepted 20 June 2023
Available online 29 June 2023
2468-8231/© 2023 Elsevier B.V. All rights reserved.
Recently, surface modification by binding ligands on catalyst has attracted growing interest as one of effective approaches to enhance the stability of metal catalysts and to investigate the IMSI influence on the performance of metal catalysts in reactions such as cyclohexene oxidation [30], CO oxidation [31,32], and CO2 reduction [33], dimethyl oxalate hydrogenation to ethylene glycol [34], methanol synthesis from CO2 [35], and also in FTS [36–38]. For instance, Chaudret et al. [36] found that the diphosphine ligands stay on the surface of Ru nanoparticles during FTS reaction and improve their selectivity toward C2−C4 hydrocarbons. In the theoretical work by Heerden et al. [37], an inversed model was constructed by binding the cluster model of the support on the metal catalyst surface to mimic the surface modification of metal catalyst by support-like ligands. They concluded that the surface modification of Co by binding alumina-based ligands increases the exposure ratio of Co(100) and Co(111), altering the crystallite morphology. DFT calculations by Zhang et al. [39] also demonstrated that carbon chain growth depends on the crystallite morphology and bulk phase. Therefore, the surface modification strategy is helpful to acquire the knowledge of the metal-support interface performance in heterogeneous catalysis.

In the silica-supported iron-based FTS, silica could be transported over the surface of iron nanoparticles under a certain pressure of steam [40,41], providing us a concept that a silica-like ligand may inevitably bind to the surface of silica-supported iron nanoparticles. On the base of this concept, Mogorosi and Steen et al. [42] employed an inverse catalyst model to experimentally study the reactivities on the iron-silica interaction in FTS by modification of nano-sized iron catalysts with well-dispersed silicate groups confirmed by infrared spectra. They found that the CO adsorption strength was reduced but the availability of hydrogen on the catalyst surface was enhanced. A similar iron-based catalyst prepared by Kishida et al. [43] produced C2 oxygenates with an extremely high selectivity, compared to the impregnation catalyst. Even so, hydrocarbons remain the main product for the iron-based FTS catalyst in the most cases. There is an open question: why formation of C2 oxygenates become easy after modifying the catalyst with silica-like ligand? One of possibilities we proposed is that the large change in the selectivity of C2 oxygenates likely happens when the catalyst surface of χ-Fe5C2 was modified by silica-based ligands, because of two reasons as below. One, χ-Fe5C2 is the well-known active phase for carbon chain growth in the iron-based FTS. The other, the silica-based ligands influence the performance of silica-supported iron-based FTS catalyst much more than the case of silica acting as the general inert support. From the viewpoint of the surface science, it is important to predict how the catalytic performance is changed and elucidate the reason why the catalytic performance is improved by binding support-like ligand on the surface of catalysts. In this case, some open questions exist: (i) what is the stable structure of the silica-ligand on the Fe5C2 surface and how about the electronic properties of the Fe5C2 surface with the silica ligand? (ii) how does the reactivity of CO dissociation influence and the reason why? (iii) why does the selectivity of the C2 oxygenates become high in the presence of the silica-ligand?

To answer the above questions, the surface modification strategy was used to theoretically study the FTS reactions at the interface of silica and χ-Fe5C2 in this work. We employed the Fe5C2(510) surface because the Miller index surface (510) taking up a large percentage among the exposed crystal facets of χ-Fe5C2 was experimentally detected by XPS and HRTEM [19,44,45], and theoretically adopted to study CH4 formation [46–48]. It is feasible and important to compare the catalytic performance of Fe5C2(510) before and after surface modification by binding silica-based ligands. Therefore, the strategy was achieved by adopting the reversed model ha-SiO2/Fe5C2(510), which was constructed by binding the hydrated silica-based ligand ha-SiO2 on Fe5C2(510). On the ha-SiO2/Fe5C2(510) interface, the reactivity of CO dissociation was investigated. To understand the formation mechanism of C2 oxygenates, C2 formation was calculated by following the carbide and CO-inserted mechanisms. To evaluate the selectivity of C2 oxygenates, the activation barrier of C2 oxygenates was compared to those of CH4 and other C2 formations. The results in the ha-SiO2/Fe5C2(510) case were compared with those in the Fe5C2(510) case to show the influence of surface modification by binding silica-like ligand on the C2 oxygenate selectivity.

2. Methods and models

2.1. Methods

DFT calculations were conducted by using Vienna ab initio simulation package (VASP) [48,49]. The interaction between electron and ion was obtained with the projector augmented wave method [50,51]. The electron exchange-correlation energy was computed under the generalized gradient approximation in the Perdew-Burke-Ernzerhof functional [52]. The kinetic energy cut of 400 eV, a first-order Methfessel-Paxton [53] electron smearing with σ = 0.2 eV and a Monkhorst–Pack k-point grid [54] of 2 x 2 x 1 were kept in all calculations. The geometry optimization was converged with the thresholds of 0.02 eV/Å and 10−4 eV for forces and energy difference, respectively. Transition states were found by the nudged elastic band method [55] and confirmed by vibrational frequencies analysis at the same theory level. The density of states (DOS) was calculated using the Gaussian smearing scheme with the smearing width of 0.01 eV. [56]. Bader charge was calculated by using the program compiled by the Henkelman group [57]. The configuration stability of the silica-modified surface was checked through ab initio molecular dynamic simulation by sampling the canonical ensemble employing Nosé–Hoover thermostats [58] with a time step of 1 fs during 4 ps of a well-equilibrated trajectory.

2.2. Models

The χ-Fe5C2 bulk structure in C2/c symmetry was rationalized with a k-points grid of 2 x 6 x 5 [59]. The crystallographic parameters a, b, c, and β were determined as 11.545 Å, 4.496 Å, 4.982 Å, and 97.6°, respectively, and magnetic moment was 1.73 μB, agreeing reasonably with the available data in experiment [60]. The used size p(3 x 1) of Fe5C2(510) supercell with the vacuum region of 15 Å contains 90Fe/36C atoms, of which the upmost 60Fe/24C atoms were relaxed and the other atoms were kept in the bulk position [54]. Table S1 validates applicability of the used slab model because the checked thickness influence little on the energy change in C + CH → CCH and C + CH2 → CCH2 reactions.

Ring sizes of α-SiO2, represented by the number n of Si atoms in the rings, distributes from 2 to 6. It was reported that the 2-membered silica ring is much less stable than the higher-membered ones [61]. Herein, the ring sizes from 3 to 6 were considered for the silica ligand on the Fe5C2(510) surface, which also ensured the surface loading of Si atoms dropping into the range (less than 4.5 atoms per nm²) evaluated by Mogorosi and Steen et al. [42] in their “inversed” experiment. Because the residual –OH groups are still presented after the high temperature calcination [62], it is reasonable to saturate the SiO4 tetrahedron by H atoms, affording Si(OH)₄. Then, the interface model of ha-SiO2/Fe5C2(510) was produced by the dehydration-dehydrogenation reaction [63] with the formation of Fe–O–Si bonds between the gaseous Si (OH)₄ molecules and the Fe5C2(510) surface (M):

\[
M (s) + n \text{SiO}_2H(g) \rightarrow \text{MSi}_n\text{O}_{3n}H_4(s) + n\text{H}_2O(g) + 0.5n\text{H}_2(g)
\]

The formed MSiₙO₃ₙH₄ structure corresponded to the interface model of ha-SiO2/Fe5C2(510) employed in this work and its thermodynamic stability was assessed by the enthalpy change (ΔE_{ave,n}) of the dehydration-dehydrogenation reaction averaged by the number n of Si atoms. The ΔE_{ave,n} term was calculated by the following equation:

\[
\Delta E_{ave,n} = [E(\text{MSi}_n\text{O}_{3n}H_4)]/n + E(\text{H}_2\text{O}) + 0.5E(\text{H}_2) - [E(M)]/n - E(\text{SiO}_2\text{H}_4)
\]
3. Results and discussions

3.1. The Fe$_3$C$_2$(510) and ha-SiO$_2$/Fe$_5$C$_2$(510) structures

The interaction between ha-SiO$_2$ and Fe$_5$C$_2$(510) occurs through Fe-O-Si bonds, with SiO$_2$ tetrahedrons binding with each other via Si–O–Si bonds at the corners. As shown in Fig. 1(a), on the clean Fe$_5$C$_2$(510) surface, there are Top (T), Bridge (B), 3-fold (3F) and 4-fold (4F) sites formed by Fe atoms for bonding with the O atoms of ha-SiO$_2$. The O atoms directly participating interfacial interaction are regarded as the interfacial O atoms. The possible configurations and the averaged reaction energies $E_{\text{ave},x}$ of ha-SiO$_2$/Fe$_5$C$_2$(510) are given in Fig. S1 of the SI. The result shows that the $E_{\text{ave},x}$ value is the most negative in the n = 4 case, indicating that the 4-membered Si ring is more stable than the other sized Si rings on the Fe$_5$C$_2$(510) surface. In the 4-membered ha-SiO$_2$/Fe$_5$C$_2$(510), the Si loading is 2.12 Si atoms per nm$^2$, which falls into the experiment range (0 ~ 4.5 Si atoms per nm$^2$) reported by Mogorosi et al. [42]. The stability of the 4-membered ha-SiO$_2$/Fe$_5$C$_2$(510) configuration under the reaction temperature (523 K) has been verified by using ab initio molecular dynamic simulation in this work, as shown in Fig. S2 of the SI. Thus, it makes sense for the 4-membered ha-SiO$_2$/Fe$_5$C$_2$(510) as a candidate model of the interface between the Fe$_5$C$_2$(510) and silica. Next, all the discussions about the ha-SiO$_2$/Fe$_5$C$_2$(510) case are based on the 4-membered ha-SiO$_2$/Fe$_5$C$_2$(510) model.

In the most stable 4-membered ha-SiO$_2$/Fe$_5$C$_2$(510), as shown in Fig. 1(b), three interfacial O atoms bind at the 3F sites and one interfacial O atom binds at the B site. The average length of the Si–O bonds in the Si–O–Si is 1.64 Å (Table S2 of the SI), which agrees with the experiment result (1.62 Å) reported by Mozzoli et al. [64]. The average bond angle of interface O–Si–O bonds (110.8°) is larger than 109.5°, indicating that stretching strain exists in the silica ring. Stretching frequencies within 758 ~ 838 cm$^{-1}$ and 842 ~ 901 cm$^{-1}$ are contributed by both the Fe–O–Si and Si–OH, while those within 929 ~ 964 cm$^{-1}$ and 3792 ~ 3821 cm$^{-1}$ are caused respectively by Si–OH and SiO–H. The frequencies 597 ~ 716 cm$^{-1}$ for Si–O–Si symmetric stretching and frequencies 988 ~ 1078 cm$^{-1}$ for O–Si–O asymmetric stretching suggest amorphous properties of ha-SiO$_2$ on Fe$_5$C$_2$(510). The latter is close to the reported typical adsorption band at 1020 cm$^{-1}$ by the oligomeric silicate species and at 1090 cm$^{-1}$ by the asymmetric O–Si–O vibration [65,66].

The Bader charge shows that in the uppermost surface of Fe$_5$C$_2$(510), Fe atoms are positively charged by 0.40 e and which is less positive than that of 0.48 e for the Fe atoms slightly below the uppermost Fe atoms. After binding the 4-membered ha-SiO$_2$ ligand, charge transfer occurs by 2.40 e from the surface Fe to the ligand SiO$_2$, causing the bonded Fe atoms with an averaged more positive charge 0.64 e. In spite of these charge transfers, the Fermi level ($\epsilon_f$) moves to a higher energy from −4.91 eV in the Fe$_5$C$_2$(510) case to −4.83 eV in the ha-SiO$_2$/Fe$_5$C$_2$(510) case, because the surface structures are greatly different. DOS analysis shows that spin-polarization of the top-layer atoms in Fe$_5$C$_2$(510) is considerably reduced after binding the ha-SiO$_2$ ligand, as shown in Fig. 2(a) and (b).

Compared to the Fe$_5$C$_2$(510) case, the $\beta$ electrons above the Fermi level are reduced obviously, suggesting that the spin-pairing interaction between the Fe$_5$C$_2$(510) and the ha-SiO$_2$ ligand occurs with unpaired electrons of the Fe and O atoms. When going from the Fe$_5$C$_2$(510) case to the ha-SiO$_2$/Fe$_5$C$_2$(510) case, the $\delta$ band center ($\epsilon_{\text{dc-VB}}$) decreases in energy from −6.45 eV to −6.81 eV and the $\delta$ valence-band center ($\epsilon_{\text{dc-VA}}$) decreases from −7.26 eV to −7.28 eV, respectively, indicating that the charge transfers from the surface to adsorbates become weak.

3.2. CO dissociation

CO dissociation starts up the FTS process. On Fe$_5$C$_2$(510), the T-site CO with the binding energy $E_b$ of −2.13 eV is more stable than those at the 4F- and 3F-site (−2.02 eV and −1.95 eV, respectively) as shown in Fig. S3 (a) of the SI. Compared to the gaseous CO, adsorption of CO at the 4F site causes the C–O bond extended most by 0.08 Å, which is regarded as the initial state of CO dissociation. CO dissociation can follow direct and H-assisted routes. The latter proceeds via the HCO intermediate by C-end hydrogenation and the COH intermediate by O-end hydrogenation. The mechanism via the HCO intermediate occurs more easily with the lower activation barrier $E_a$ than that by the COH intermediate [67,68]. As shown in Figs. 3 and S4 (a) of the SI, the 4F-site CO dissociation needs the $E_a$ 1.17 eV by the direct route. In the H-assisted route via forming the HCO intermediate, HCO formation needs the $E_a$ 1.45 eV with an endothermicity by 0.89 eV; cleavage of the C–O bond in HCO needs a low $E_a$ 0.57 eV but is strongly exothermic (1.33 eV). Thus, the $E_a$ value (1.46 eV) for CO dissociation via the HCO intermediate is larger than that by the direct route, similar to the reported result by Pham et al. [67]. We thus concluded that CO dissociation is mainly in the direct route on Fe$_5$C$_2$(510).

In the ha-SiO$_2$/Fe$_5$C$_2$(510) case, the originally preferred 4F-site for the dissociated C from CO at the T-site is occupied by the interface silica, thus hindering the T-site CO dissociation. Alternatively, the CO on the interface of ha-SiO$_2$/Fe$_5$C$_2$(510) is stably located at the interface 3F$_s$ site with the $E_b$ value −2.12 eV, as shown in Fig. S3 (b) of the SI, which is more negative than that at −1.95 eV at the similar 3F site on Fe$_5$C$_2$(510). The result shows that the CO molecule binds more strongly to the interface Fe atom in the ha-SiO$_2$/Fe$_5$C$_2$(510) case than that in the Fe$_5$C$_2$(510) case; It is reasonable because the distance between the H atom of the interface Si–O–H and the O atom of the CO molecule is 2.47 Å, indicating the hydrogen bond interaction. The energy profile of the 3F$_s$-site CO dissociation, as given in Figs. 3(b) and S4 (b) of the SI, indicates that the H-assisted CO dissociation via the HCO intermediate overcomes the $E_a$ 1.39 eV to form the HCO intermediate with an endothermicity of 0.85 eV and continues to surpass an $E_a$ 0.99 eV for breaking the C–O bond of the HCO intermediate. Additionally, the O-end hydrodgenation is difficult because the adsorption geometry of CO molecule is in vertical orientation to the surface like the case in the Fe$_5$C$_2$(510)
Thus, the $E_a$ value (1.84 eV) for the H-assisted CO dissociation is smaller than that for CO direct dissociation (2.65 eV). The result suggests that on the interface of ha-SiO$_2$/Fe$_5$C$_2$(510), the H-assisted route via the HCO intermediate is easier than the CO direct dissociation, but is more difficult than the CO dissociation on the clean surface of Fe$_5$C$_2$(510). We therefore concluded that the H-assisted CO dissociation occurs on the interface of ha-SiO$_2$/Fe$_5$C$_2$(510).

The above results show that CO dissociation becomes difficult as the cases going from Fe$_5$C$_2$(510) to ha-SiO$_2$/Fe$_5$C$_2$(510) and we explained the reason(s) why as follows. Even for the 3F-site CO on Fe$_5$C$_2$(510), the $E_b$ value is just less negative than that of the T-site CO (by 0.18 eV), which is still much smaller than the increase for the $E_a$ value of CO direct dissociation (by 1.50 eV), suggesting that the inaccessibility of the originally preferred 4F$_1$-site for the CO dissociation is not the main reason. Before CO adsorption, the CO-bonded two Fe atoms have the positive charges increased from 1.00 e to 1.02 e as the cases going from Fe$_5$C$_2$(510) to ha-SiO$_2$/Fe$_5$C$_2$(510), which does not favor CO activation. In another perspective, CO dissociation is regarded as the oxidative addition of CO to Fe. There occurs charge transfer by 2.40 e from the surface Fe to the ligand SiO$_2$ and lowers the $\epsilon_{dc}$-VB value of Fe from 7.26 eV to 7.28 eV, which does not favor the oxidative addition of CO to Fe, because the oxidative addition usually gets difficult when the valence orbital energy of metal catalysts is lowered.

### 3.3. CH$_4$ formation

Methane is an undesired but inevitable product of the FTS. CH$_4$ formation contains multi-step elementary reactions in experiment, which could happen through the step-wised hydrogenations by the surface C and the additional C from CO dissociation. Methanation energy profiles for the surface C and the additional C on CO dissociation were discussed below.

In the Fe$_5$C$_2$(510) case, there are two kinds of the upmost C atoms, respectively at the Fe-rich region and Fe-poor region (Fig. S5 of the SI). The two kinds of C atoms have the similar Bader charges (–1.08 e and –1.04 e), the similar activation barriers ($E_{a\_eff}$, CH$_4$) of CH$_4$ formation (3.58 eV and 3.51 eV), and the similar increasing trends of total energy in the reaction coordinate, where the lowest energy point is by the H adsorption around the C atom and the highest energy point is by the transition state (TS) for the final hydrogenation (Fig. S5 of the SI). Herein, we mainly discussed the methanation of the upmost C atom at the Fe-rich region, marked by C$_O$ in Fig. 4 (a), because the H element prefers the Fe-rich region more than the Fe-poor region. An additional C (marked by C$_A$) from CO dissociation is left at the 4F-site and its methanation is further employed. CH$_4$ formation processes of C$_O$ and C$_A$ (marked by R$_C$ and R$_C^A$, respectively) on Fe$_5$C$_2$(510) are presented by Fig. 4(b), with the TS structures for each hydrogenation step given in Fig. S6 of the SI and detailed energy parameters shown in Table S3 of the SI. The C$_A$ adsorption causes the H adsorption energy changed from
–0.71 eV to –0.59 eV. On routes of R_C^0 and R_C^1, similar increasing tendencies of hydrogenation coordinate were found for the hydrogenation TSs with the highest total energy at the TS4. Accordingly, the \( E_{\text{eff}}^{\text{CO}, \text{CH}4} \) value is the RE difference between the surface C + 4H and the TS4 of CH₃ hydrogenation. The C^0 compared to the C^0 has a lower \( E_{\text{eff}}^{\text{CO}, \text{CH}4} \) (2.23 eV vs. 3.07 eV), which was ascribed to the less steric hindrance from interface ha-SiO₂ for the H attacking in the methanation process confirmed by the more stable intermediates and lower TS energies on the R_C^0. These results showed that CH₄ formation by the additional C^0 hydrogenations are easier than that by the interface C^0 hydrogenations.

In the case of ha-SiO₂/Fe₅C₂(510), the existence of 4-membered ha-SiO₂ makes the interface C in different coordination environment. In the ha-SiO₂/Fe₅C₂(510) case, three kinds of interface C atoms, marked by C^0–1, C^0–2, and C^0–3, are close to Fe–O–Si bonds, as shown in Fig. S7 of the SI. The interface C^0–1 is close to one 2F-site O atom; the interface C^0–2 is close to one 2F-site O atom and one 3F-site O atom; the interface C^0–3 is close to two 3F-site O atoms. The C^0–1, C^0–2, and C^0–3 atoms are charged by \( -0.04 \), \( -0.01 \), and \( -0.17 \) e, respectively, and are less negative than the charge \( -1.08 \) e for the surface C at the Fe-rich region on Fe₅C₂(510) because of the charge transfer from the surface Fe to the ha-SiO₂ ligand. Around the C^0–1, C^0–2, and C^0–3, the most stable H atom is located at nearby 3F₁, 3F₂, and 3F₃ sites, respectively with \( E_0 \) values of \(-0.70\) eV, \(-0.68\) eV, and \(-0.54\) eV. Energy profiles (Fig. S7), the TS structures in Fig. S8, and energy parameters in Table S3 of the SI for methanation for the interface C^0–1, C^0–2, and C^0–3 are shown by R_C^0–1, R_C^0–2, and R_C^0–3, respectively. CH₄ formation by the route R_C^0–1 has the \( E_{\text{eff}}^{\text{CO}, \text{CH}4} \) of 3.26 eV, higher than those of 3.07 eV and 3.00 eV, respectively by the routes R_C^0–2 and R_C^0–3. Because the route R_C^0–2 has advantages in stability of the adsorbed H₂, intermediates of CH and CH₂, and the four TSs, the interface C^0–2 is relatively easier to be mechanized. Therefore, the adsorption sites for an additional C (marked by C^0) is mainly confined around the interface C–2 (newly marked by C^0) in Fig. 4(c). The additional C^0 located at the 3F-site around the CO₃ atom is stable, as shown by Fig. S3 (c) of the SI. Methanation energy profiles for CO₃ (R_C^0–3) and CO₃ (R_C^0–4) are shown in Fig. 4(d) with the corresponding TS structures in Fig. S9 and energy parameters in Table S3 of the SI. The R_C^0 compared to the R_C^0 has the lower \( E_{\text{eff}}^{\text{CO}, \text{CH}4} \) (2.30 eV vs. 3.07 eV), which was ascribed to the less steric hindrance from interface ha-SiO₂ for the H attacking in the methanation process confirmed by the more stable intermediates and lower TS energies on the R_C^0. These results showed that CH₄ formation by the additional C^0 hydrogenations are easier than that by the interface C^0 hydrogenations.

3.4. \( C_2 \) formation

Ability of \( C_2 \) formation was compared in between the Fe₅C₂(510) and ha-SiO₂/Fe₅C₂(510) cases by investigating C₁ + C₂ coupling following carbide (CH₄ + CH₄ → CH₂CH₂; i and j = 0 ~ 3) and CO-insertion (CO + CH₄ → COCH₂; j = 0 ~ 3) mechanisms. C₁ + C₂ coupling was calculated for the surface C^0 and adsorbed C^0 in Fig. 4(a) and the surface C^0 and adsorbed C^0 in Fig. 4(c); the superscripts “O” and “A” are used to denote the C is the original atom in the surface and the additional atom from CO dissociation, respectively; the superscripts “i” and “j” is used to distinguish the ha-SiO₂/Fe₅C₂(510) case from the Fe₅C₂(510) case. Because hydrogenation is much easier by C^0 (or C^0) than that by C^0 (or C^0), as suggested by Fig. 4, the CH₄ + CH₄ coupling in the \( i \leq j \) case was calculated as C^0CH₄ + C^0CH₄ (or C^0CH₄ + C^0CH₄). With the reference of three gaseous H₂ molecules, energy profiles of \( C_2 \) formation were presented in Fig. S. The corresponding structures about the IS, TS, and FS, together with the \( E_0 \) and \( E_1 \) values were given in Figs. S10 and S11 of the SI. On the energy profiles, the highest TS energy for CH₄ formation was also calibrated for comparison convenience.

From the energy profiles in Fig. 5(a), the CCH, CHCH and CCO species are found to be more stable than other \( C_2 \) species in thermodynamics on the surface of Fe₅C₂(510). In kinetics, the carbide mechanisms involved with CH₂ and CH₂ have the higher effective barriers than that of 2.23 eV for CH₄ formation, because of the energetic instability of CH₂ and CH₂ as well as the steric repulsion between H-rich C₁ intermediates [69]. Thus, CH₂ and CH₂ are not active species for carbon chain growth on this surface. The C + C, C + CH, and CH + CH couplings have lower effective barriers than that of 2.23 eV for CH₄ formation,
suggested that these couplings might be the major coupling pathways. The C + CH coupling with the lowest effective barrier of 1.47 eV is regarded as the most feasible carbide mechanism, which is in agreement with the literature report [46]. CO-inserted mechanisms by CH₂ + CO and CH₃ + CO couplings have higher effective barriers, and the C + CO and CH + CO couplings have the lower effective barriers than that of 2.23 eV for CH₄ formation. The CHO species produced by the CO hydrogenation in the H-assisted CO dissociation also might take part in C₁ + C₁ coupling but the process hardly occurs due to thermodynamic instability implied by the high energy in energy profiles of CO dissociation. One should aware that the CO-inserted mechanism is in competition with CO dissociation. The lower barrier for CO dissociation compared to the C + CO coupling means that the C–O bond could have been broken before the CO-inserted mechanism (1.15 eV vs. 1.68 eV). Therefore, it can be concluded that the CO-inserted mechanism is infeasible and less C₂ oxygenate will be produced on the clean Fe₅C₅(510) surface.

On the interface of ha-SiO₂/Fe₅C₅(510), as shown in Fig. 5(b), the CC, CCH, CCH₂, CCH₃, CHCH, and CCO exhibit energetic advantages over other C₂ species. The couplings with CH₂ and CH₃, excluding the C + CH₂ and C + CH₃ couplings, are difficult to occur because of higher effective barriers. The effective barriers for carbide routes by C + C, C + CH, C + CH₂, C + CH₃, CH + CH, and CH + CH₂ couplings are lower than that of 2.30 eV for CH₄ formation, and get the minimum of 1.96 eV by the C + CH₃ coupling. Therefore, the C + CH₃ coupling is the most feasible carbide mechanism. CO-inserted mechanisms could be facilitated on the ground that CO dissociation is difficult on the interface of ha-SiO₂/Fe₅C₅(510). Among the CO-inserted routes, the C + CO coupling has the lowest effective barrier of 1.58 eV, making it more accessible than other CO-inserted routes. Considering the energetic advantage of the HCO intermediate in the process of CO dissociation, the coupling with HCO is also considered but hardly occurs, as demonstrated by the C + CHO coupling with a higher effective energy (3.26 eV) than that for CH₄ formation, as shown in Fig. 6. Because both the CH₄ hydrogenation and CO hydrogenation need too much energy, the CH₄ + CHO coupling is not so favorable as the C + CO coupling. The C + CO coupling has lower barriers than the most possible direct route for CO dissociation (1.56 eV vs. 2.78 eV, respectively). Also, cleavage of C–O bond in the CCO is difficult with the high effective barrier (3.27 eV). The results imply that the C–O bond is difficult to activate on the interface of ha-SiO₂/Fe₅C₅(510) either by direct and H-assisted CO dissociation or after coupling with interface C₁ species. As such, this interface facilitates C + CO coupling as the most feasible pathway for C₁ + C₁ coupling with the CCO as one important C₂ oxygenate.

Above results showed that on the Fe₅C₅(510) surface, the most feasible carbide mechanism occurring by the C + CH coupling has the effective barrier (1.47 eV) lower than that of the most feasible CO-inserted mechanism occurring by the C + CO coupling (1.68 eV), by 0.21 eV. At the interface of ha-SiO₂/Fe₅C₅(510), the most feasible carbide mechanism occurring also by the C + CH coupling has the effective barrier (1.98 eV) higher than that of the most feasible CO-inserted mechanism occurring by the C + CO coupling (1.56 eV), by 0.42 eV. Thus, we concluded that the reaction pathway is shifted from the carbide mechanism (the C + CH coupling) to the CO-inserted mechanism (the C + CO coupling) after silica modification.

To understand the reason(s) for the shift in the reaction pathway after silica modification, it is necessary to make it clear that why the effective barrier is increased for the C + CH coupling (by 0.51 eV from
1.47 eV to 1.98 eV) and decreased for the C + CO coupling (by 0.12 eV from 1.68 eV to 1.56 eV). When the case goes from the Fe5 atoms directly binding with the C and CH species considerably gets shorter by 0.481 Å (from 3.005 Å to 2.514 Å), which agrees well with the result that the interaction between the C and CH species gets weaker, suggesting that the silica modification suppresses the deformation of the surface caused by the forming C–CH bond from the IS to the TS and therefore the C + CH coupling becomes difficult when the case changes from the Fe5C2(510) surface to the interface of ha-SiO2/Fe5C2(510).

The above analysis shows that the silica modification suppresses both the deformation of the surface caused by the forming C–C bond in the carbide mechanism and the C–O bond cleavage in the CO-inserted mechanism, thus resulting in the shifting of the reaction pathway from the carbide mechanism (the C + CH coupling) to the CO-inserted mechanism (the C + CO coupling) after silica modification.

3.5. Selectivity of CH4 and C2 oxygcnation

In order to assess the selectivity of CH4 and C2 species in FTS, few well-accepted assumptions according to literatures was made as follows [70–75]. With steady-state approximations, the reactions prior to the hydrogenation of CH3 are in quasi-equilibrium and the hydrogenation of CH3 with the highest energy of TS is the rate-determining step for CH4 formation. Our calculation results of CH4 formation and C1 + C1 coupling show that the CH4 hydrogenation is easier than the C–C bond formation by either the carbide mechanism or the CO-inserted mechanism. Under typical FT reaction conditions, the C1 + C1 coupling reactions are usually considered to be irreversible, desorption of the hydrogenated hydrocarbon is the rate-determining step, and thus the hydrogenation reactions are in quasi-equilibrium at steady-state prior to hydrocarbon desorption. On the basis of these assumptions and following micro-kinetcs proposed by Hu group [70,76] and widely used in literatures [46,54,77,78], the larger positive value of \( \Delta E_{a_{\text{eff}}} = E_{a_{\text{eff}} - \text{CH}_4} - E_{a_{\text{eff}} - \text{C}_1 + \text{C}_1} \) means that C2 formation occurs more easily, where the terms \( E_{a_{\text{eff}} - \text{CH}_4} \) and \( E_{a_{\text{eff}} - \text{C}_1 + \text{C}_1} \) are the effective barriers for the formations of CH4 and C2 species, respectively; More details of the micro-kinetcs on CH4 formation and C1 + C1 coupling are given in the Page S17 of the SI.

C1 + C1 coupling in the Fe5C2(510) case mainly follows the carbide route of C + CH coupling and in the ha-SiO2/Fe5C2(510) case mainly

Fig. 7. The change of interaction energies between the C + CH moiety and the rest moiety as going from the Fe5C2(510) surface to the ha-SiO2/Fe5C2(510) interface and the geometry parameters of the transition state (TS) in the Fe5C2(510) case and TS’ in the ha-SiO2/Fe5C2(510) case. All the energies are in eV and the distances are in Å.
follows CO-inserted route of C + CO coupling. Based on the most feasible coupling, the $\Delta E_{\text{eff}}$ value in the ha-SiO$_2$/Fe$_5$C$_2$(510) case is just smaller by 0.01 eV than that in the Fe$_5$C$_2$(510) case, indicating the similar selectivity of CH$_4$ to C$_2$ in the two cases. On the Fe$_5$C$_2$(510) surface, CO-inserted mechanisms are nearly infeasible for C$_1$ + C$_1$ coupling because CO dissociation is easy, and thus the main C$_2$ product is O-contained. On the ha-SiO$_2$/Fe$_5$C$_2$(510) interface, C$_1$ + C$_1$ coupling can follow the CO-inserted route, indicating that the main C$_2$ product is O-contained. Compared to the Fe$_5$C$_2$(510) case, the C$_2$ oxygenate selectivity is enhanced in the ha-SiO$_2$/Fe$_5$C$_2$(510) case. From the viewpoint of structural properties, the ha-SiO$_2$ ligand covers the active site and anchors CO at the inactive site via the hydrogen bond, thus hindering the CO dissociation but promoting the CO-inserted mechanism. From the viewpoint of electronic properties, the d-valence band center lowers in energy when the Fe$_5$C$_2$(510) surface is modified with the ha-SiO$_2$ ligand, which does not favor the C-O bond cleavage for both CO molecule and COO species, because usually the oxidative addition is suppressed when the d orbital of metal catalysts exists at a low energy and the C-O bond cleavage is understood to be oxidative addition. The result is in agreement with the experimental result that the selectivity of C$_2$ oxygenates is higher for the iron catalysts modified with silica in w/o micro-emulsions than that for the impregnated catalysts [43]. However, the reactive sites provided by the iron carbide are generally more active than those sites close to the silica species in terms of the FTS activity and in most cases the carbide mechanism remains the main route for carbon chain growth for the whole catalyst of iron carbide after silica modification. Our results could enrich the knowledge of the intrinsic catalytic role(s) of the interface between the iron carbide catalysts and the support of silica in the FTS.

4. Conclusion

In this work, we theoretically investigated surface modification of Fe$_5$C$_2$ by silica-based ligand and its influence on C$_2$ oxygenate selectivity in the Fischer-Tropsch Synthesis by carrying out a theoretical study of CO dissociation, CH$_4$ formation and C$_1$ + C$_1$ coupling on the Fe$_5$C$_2$(510) surface and the ha-SiO$_2$/Fe$_5$C$_2$(510) interface. The inverted model of ha-SiO$_2$/Fe$_5$C$_2$(510) is constructed by assuming the dehydride-dehydrogenation reaction occurring between the Si(OH)$_4$ gas molecules and the Fe$_5$C$_2$(510) surface with the formation of Fe-O-Si bonds on the interface. It was found that CO dissociation on the clean model is easier by the direct route than that by the H-assisted route. CH$_4$ formation was calculated for the upmost C and the additional C from CO dissociation on two modes of the clean surface of Fe$_5$C$_2$(510) and the interface of ha-SiO$_2$/Fe$_5$C$_2$(510). On the two modes, the additional C is easier to be hydrogenated into CH$_4$ than the upmost C. The C$_1$ + C$_1$ coupling proceeds by the carbide mechanism with C + CH coupling as the most feasible route instead of the CO-inserted mechanisms because CO dissociation is easy.

On the interface of ha-SiO$_2$/Fe$_5$C$_2$(510), the CO dissociation becomes difficult because the d-valence band center decreases when binding with the ha-SiO$_2$ ligand. The ha-SiO$_2$ anchors CO via the hydrogen bond, which hinders the CO dissociation but facilitates the CO coupling with interface C. Meanwhile, the silica modification suppresses the deformation of the surface caused by the forming C–CH bond from the BS to the TS and thus the C + CH coupling becomes difficult when the case changes from the surface of Fe$_5$C$_2$(510) to the interface of ha-SiO$_2$/Fe$_5$C$_2$(510). Therefore, the interface changes the main pathway of C$_1$ + C$_1$ coupling into the CO-inserted mechanism with formation of C$_2$ oxygenates as the cases going from the clean surface of Fe$_5$C$_2$(510) to the interface of ha-SiO$_2$/Fe$_5$C$_2$(510). The similar selectivity of CH$_4$ and higher selectivity of CCO on the ha-SiO$_2$/Fe$_5$C$_2$(510) interface were concluded by comparing the effective barrier difference between CH$_4$ formation and C$_1$ + C$_1$ coupling to that on the clean surface of Fe$_5$C$_2$(510). The enhanced selectivity of C$_2$ oxygenates was ascribed to the reduced reactivity of the C + CH coupling and the C–O bond cleavage. Note that the reactive sites provided by the iron carbide are generally responsible for the FTS activity and in the most cases the carbide mechanism remains the main route for carbon chain growth for the whole catalyst of iron carbide after silica modification. Our results provided some helpful insights for understanding the influence on catalytic selectively by surface modification of silica ligand on the silica-supported iron carbide catalysts in the FTS.

Influence of the slab thickness on coupling reactions on Fe$_5$C$_2$(510) (Table S1); parameters about the silica rings on Fe$_5$C$_2$(510) (Table S2); energy parameters about CH$_4$ formation on the clean surface and the interface (Table S3); inversed modes and energies of interface structures (Fig. S1); the stability of the interface structure under the reaction temperature (Fig. S2); adsorption of C and CO on the interface (Fig. S3); Geometry changes of the CO dissociation (Fig. S4); methanation energy profiles and adsorption structures of the H atom, intermediates, and TS along the coordinate of CH$_4$ formation on the clean surface and the interface (Figs. S5 – S9); energies and structures for C$_1$ + C$_1$ couplings on the clean surface and the interface (Figs. S10 and S11). Interaction-deformation energies analysis; Microkinetic analyses.

CRediT authorship contribution statement

Junqing Yin: Conceptualization, Data curation, Investigation, Visualization, Formal analysis, Methodology, Validation, Writing – original draft, Writing – review & editing, Project administration, Resources, Supervision, Funding acquisition. Shuyuan Wang: Conceptualization, Writing – review & editing, Funding acquisition. Dan Xu: Conceptualization, Writing – review & editing, Yong You: Writing – review & editing. Xingchen Liu: Conceptualization, Methodology, Software, Writing – review & editing. Qing Peng: Conceptualization, Methodology, Software, Writing – review & editing.

Declaration of Competing Interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

Data availability

Data will be made available on request.

Acknowledgments

The authors are grateful for the Natural Science Foundation of Sichuan Province (No. 2023NSFSC1080), the Talent Program of Chengdu University (No. 2081923010), Qilu University of Technology (Shandong Academy of Sciences) Project (NO. 2022BZ02–03), and the funding support from Synfuels China Co. Ltd.

Supplementary materials


References


